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MEVD - 204 M.E./M.Tech., II Semester

Examination, June 2013

Micro Electronics

Time: Three Hours

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Maximum Marks: 70

Note: Answer all questions. Section (a) is compulsory from each question. Asswer two sections from each question. All questions carry equal marks.

- 1. a) Explain different effects produced due to charge transportation in a semi conductor 7
 - b) Describe importance of arrangement of atoms in the semiconductor materials.
 - c) Discuss motion of electron in a periodic lattice.
- 2. a) Applying the quantum concepts, derive the schrodinger wave equations.
 - b) Explain carrier generation and recombination theory. 7
 - c) Derive expression to determine Fermi level and also draw label diagram.
- 3. a) Differentiate between elemental and compound semiconductors. Also describe the principle of probability and uncertainty.

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| | b) | Derive the complete expression of continuity equation | n. |
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| | | | 7 |
| | c) | Effects of temperature on mobility and conductivity. | 7 |
| ŀ. | a) | Discuss Boltzmann Transports equation. | 7 |
| | b) | Explain Ebers-moll model for modeling of BJT. | 7 |
| | c) | What are heterojunction bipolar transistors? How do it successfully operate at high frequencies. | es 7 |
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| | a) | Discuss BJT modeling using nonuniform doping. | 7 |
| | b) | Derive expression for all types of capacitances associate with p-n junction. | ed 7 |
| | c) | Explain small signal model of BJT with CE configuration | on. 7 |
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